



GaAs monolithic integrated driver amplifier

0.9~1.3GHz

**key indicator**

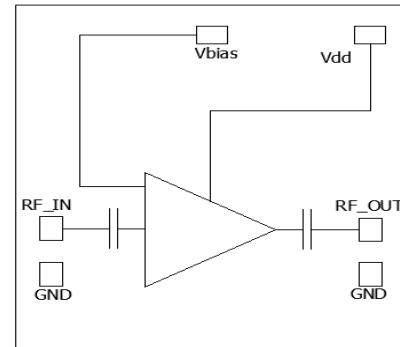
- Frequency range: 0.9~1.3GHz
- Gain: 20dB
- Output  $P_{1\text{dB}}$ : 26dBm
- Single power supply operation: +8V@142mA
- Chip size: 1.1mm×1.25mm×0.1mm

**typical application**

- Point-to-point communication
- Satellite Communications
- Military and aerospace
- Testing and measuring instruments
- radar

**Product Introduction**

AY1567 amplifier chip works from 0.9 to 1.3 GHz and is made of GaAS technology. Under 142mA working current, it can provide 20.2dB gain, 26dBm output  $P_{1\text{dB}}$ , and the noise in the normal temperature band is lower than 3.4dB. The chip uses on-chip metal chemical technology to ensure good grounding, and the back of the chip is metalized, which is suitable for eutectic sintering or conductive adhesive bonding processes.

**Functional block diagram****Electrical performance (T<sub>A</sub>=25°C, V<sub>D</sub>=+8V, ID=142mA, Z<sub>0</sub>=50Ω)**

index	Minimum	Typical value	Max	unit
frequency		0.9 ~ 1.3		GHz
Small signal gain	-	20.2	-	dB
Small signal gain flatness	-	0.4	-	dB
Reverse isolation	-	-27	-	dB
Input/output standing wave ratio	-	1.4	-	:one
Noise Figure	-	3.4	-	dB
Output P <sub>1dB</sub>	-	26	-	dBm
Output IP <sub>3</sub>	-	36	-	dBm
Working current	-	142	-	mA

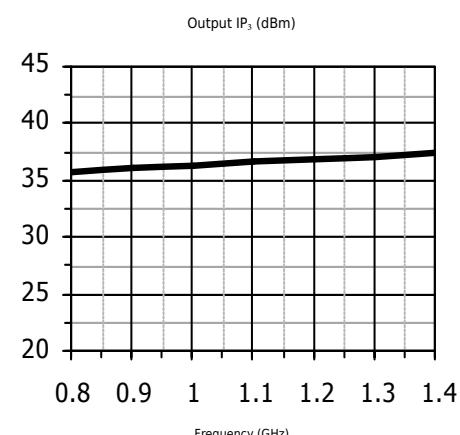
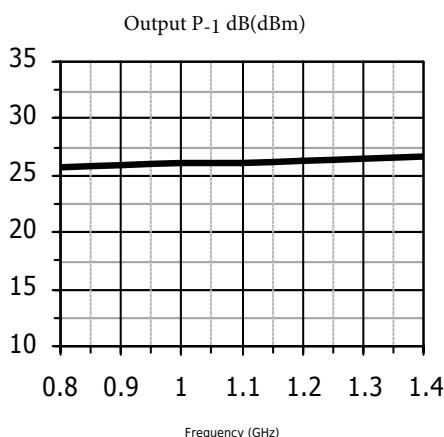
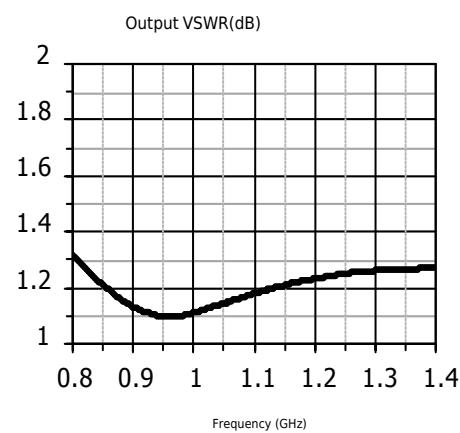
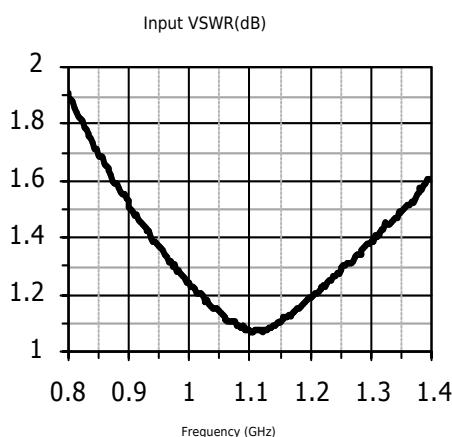
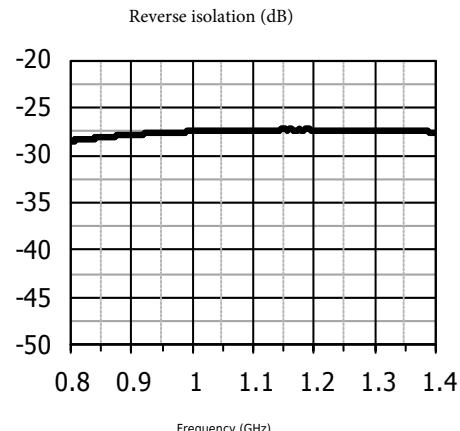
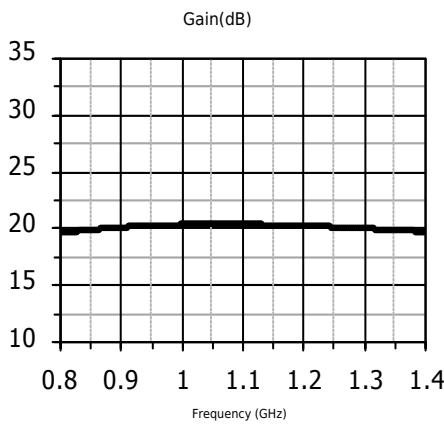
**Absolute maximum rating**

Maximum input power	+18dBm	Operating temperature	-55 °C ~ + 85 °C
Channel temperature	150 °C	Storage temperature	-65 °C ~ + 150 °C



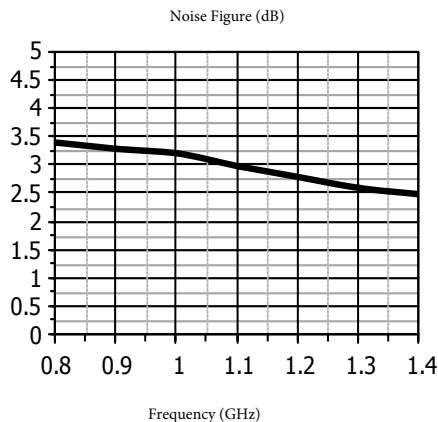
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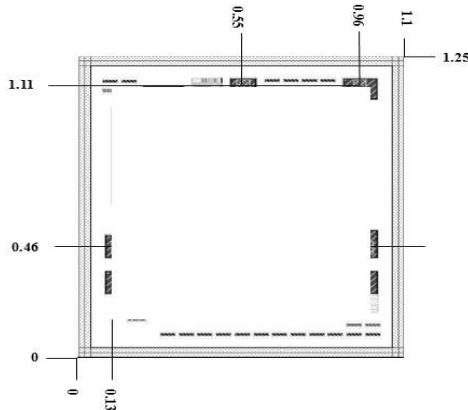
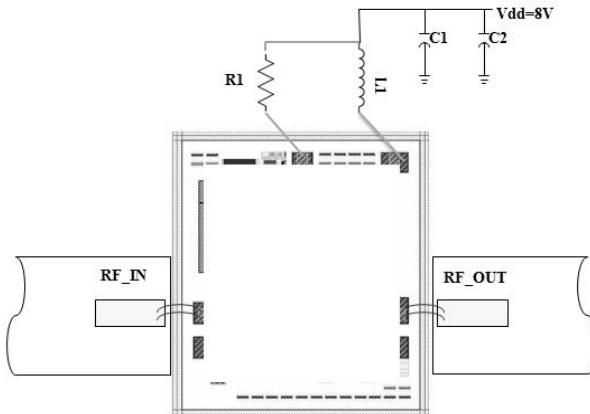
**Typical test curve**

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**Component list**

serial number	Numerical value	model	manufacturer	Encapsulation
R1	300Ω	-	-	0603
C1	330pF	GRM1885C1H331JA01	Murata	0603
C2	10nF	GRM1857U1A103JA44	Murata	0603
L1	10nH	0603LS10NXJLC	Thread art	0603

**Shape and port size (mm)****Recommended assembly drawing****Precautions**

Gallium arsenide MMIC devices are susceptible to electrostatic discharge damage. Precautions should be taken during transportation, assembly and testing.